

IN THE CLAIMS

This listing of claims will replace all prior versions, and listing, of claims in the application:

Listing of Claims:

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1. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate;

a first well of a prescribed conductivity type at which a first active element is provided, said first well being selectively formed in a surface of said semiconductor substrate;

a second well of the same conductivity type as said prescribed conductivity type at which a second active element is provided, said second well being selectively formed in said surface of said semiconductor substrate and adjacent to said first well;

a first conductive layer across said first well and said second well in said surface of said semiconductor substrate with an end provided on said first well and another end provided on said second well, said first conductive layer electrically connecting said first well and said second well;

a first contact situated directly above said first well; and

a second contact situated directly above said second well;

wherein said first and second contacts are connected to a single potential and the first conductive layer has the same conductivity type as said prescribed conductivity type of said first and second wells.

2. (Original) The semiconductor device according to claim 1, wherein said first contact is in contact with said first conductive layer.

3. (Previously Presented) The semiconductor device according to claim 2, wherein said second contact is in contact with said first conductive layer.

4. (Original) The semiconductor device according to claim 3, wherein said first contact is arranged in opposition to said first well through said first conductive layer while said second contact is arranged in opposition to said second well through said first conductive layer.

5. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate;  
a first well of a prescribed conductivity type at which a first active element is provided, said first well being selectively formed in a surface of said semiconductor substrate;

Q1 a second well of the same conductivity type as said prescribed conductivity type at which a second active element is provided, said second well being selectively formed in said surface of said semiconductor substrate and adjacent to said first well;

a first conductive layer across said first well and said second well in said surface of said semiconductor substrate with an end provided on said first well and another end provided on said second well, said first conductive layer electrically connecting said first well and said second well;

a first contact electrically connected with said first well; and

a second conductive layer formed in said surface of said semiconductor substrate and provided on said first well without being in contact with said second well,

wherein said first contact is in direct contact with said second conductive layer and the first conductive layer has the same conductivity type as said prescribed conductivity type of said first and second wells.

6. (Original) The semiconductor device according to claim 1, wherein

said first conductive layer includes at least one of an impurity introduction layer of the same conductivity type as said prescribed conductivity type and a compound layer of the material for said semiconductor substrate and a metal.

7. (Original) The semiconductor device according to claim 6, wherein said first conductive layer has lower resistivity than said first well and said second well.

8. (Original) The semiconductor device according to claim 5, wherein said second conductive layer includes at least one of an impurity introduction layer of the same conductivity type as said prescribed conductivity type and a compound layer of the material for said semiconductor substrate and a metal.

DI 9. (Original) The semiconductor device according to claim 8, wherein said second conductive layer has lower resistivity than said first well.

10. (Amended) The semiconductor device according to claim ~~[[3]]~~ 1, wherein said first well and said second well have different impurity profiles.

11. (Previously Presented) The semiconductor device according to claim 1, wherein the first and second semiconductor elements are first and second transistors respectively.

12. (Previously Presented) The semiconductor device according to claim 5, wherein said second well is deeper than said first well.

13. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate;  
a first well of a prescribed conductivity type selectively formed in a surface of said semiconductor substrate and including a first active element;

a second well of the same conductivity type as said prescribed conductivity type selectively formed in a surface of said semiconductor substrate and adjacent to said first well, and including a second active element;

DI a conductive layer across said first well and said second well in said surface of said semiconductor substrate with an end provided on said first well and another end provided on said second well, said conductive layer of the same conductivity type as said prescribed conductivity type and including a compound layer of the material for said semiconductor substrate and a metal; and

a first and second contacts directly connected to said conductive layer and connected to a single potential.

14. (Previously Presented) The semiconductor device according to claim 13, wherein said conductive layer further includes an impurity introduction layer of the same conductivity type as said prescribed conductivity type positioned under said compound layer.

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